Transistors

Switching (-30V, -9.0A)

RSS090P03

Features

- 1) Low On-resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small and Surface Mount Package (SOP8).

Application

Power switching, DC / DC converter.

●Structure

Silicon P-channel MOS FET

Packaging specifications

	Package	Taping
Type	Code	TB
	Basic ordering unit (pieces)	2500
RSS090P03	0	

● Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit	
Drain-source voltage		V _{DSS}	-30	V	
Gate-source voltage		Vgss	±20	V	
Drain current	Continuous	ID	±9.0	Α	
	Pulsed	IDP	±36	A *1	
Source current (Body diode)	Continuous	Is	-1.6	Α	
	Pulsed	I _{SP}	-36	A *1	
Total power dissipation		PD	2.0	W *2	
Channel temperature		Tch	150	°C	
Range of Storage temperature		Tstg	-55 to +150	°C	

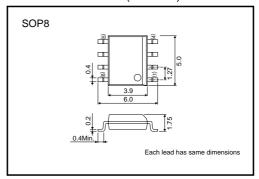
^{*1} Pw≤10μs, Duty cycle≤1% *2 Mounted on a ceramic board

●Thermal resistance (Ta=25°C)

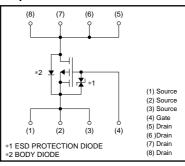
Parameter	Symbol	Limits	Unit
Channel to ambient	Rth (ch-a)	62.5	°C / W *

^{*} Mounted on a ceramic board.

●External dimensions (Unit : mm)



●Equivalent circuit



●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	I _{GSS}	_	-	±10	μΑ	V _{GS} =±20V, V _{DS} =0V
Drain-source breakdown voltage	V _(BR) DSS	-30	_	_	V	I _D = -1mA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	-	_	-1	μΑ	V _{DS} = -30V, V _{GS} =0V
Gate threshold voltage	V _{GS (th)}	-1.0	_	-2.5	٧	V _{DS} = -10V, I _D = -1mA
Static drain-source on-state resistance		_	10	14	mΩ	I _D = -9.0A, V _G S= -10V
	R _{DS (on)} *	_	15	21	mΩ	I _D = -4.5A, V _G S= -4.5V
		-	17	23	mΩ	I _D = -4.5A, V _G s= -4.0V
Forward transfer admittance	Y _{fs} *	6.0	_	_	S	V _{DS} = -10V, I _D = -4.5A
Input capacitance	Ciss	-	4000	_	рF	V _{DS} = -10V
Output capacitance	Coss	-	750	_	pF	V _{GS} =0V
Reverse transfer capacitance	Crss	-	580	_	pF	f=1MHz
Turn-on delay time	t d (on) *	_	25	_	ns	I _D = -4.5A
Rise time	tr *	-	50	_	ns	VDD≒ -15V
Turn-off delay time	t _{d (off)} *	-	150	_	ns	VGS= −10V RL=3.3Ω
Fall time	t _f *	_	80	_	ns	Rgs=10Ω
Total gate charge	Qg	_	39	-	nC	V _{DD} ≒−15V
Gate-source charge	Qgs	_	7.0	-	nC	V _{GS} =-5V
Gate-drain charge	Q _{gd}	_	15	-	nC	I _D =-9.0A

*Pulsed

Body diode characteristics (source-drain characteristics)

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Forward voltage	Vsn	_	_	-12	V	Is= -1 6A Vcs=0V

Electrical characteristic curves

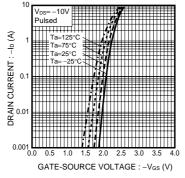


Fig.1 Typical Transfer Characteristics

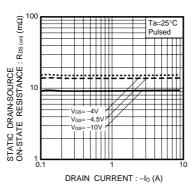


Fig.2 Static Drain-Source On-State Resistance vs. Drain Current

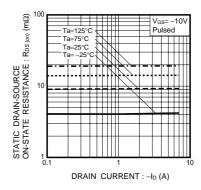


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current

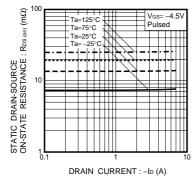


Fig.4 Static Drain-Source On-State vs. Drain Current

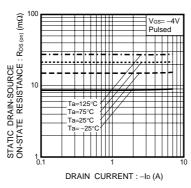


Fig.5 Static Drain-Source On-State vs. Drain Current

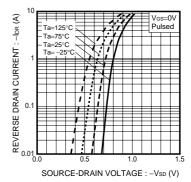


Fig.6 Reverse Drain Current Source-Drain Current

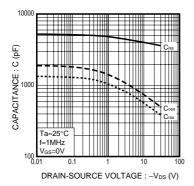


Fig.7 Typical Capacitance vs. Drain-Source Voltage

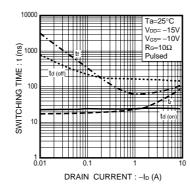


Fig.8 Switching Characteristics

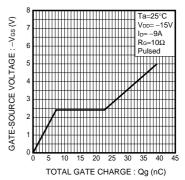


Fig.9 Dynamic Input Characteristics

●Measurement circuits

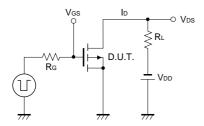


Fig.10 Switching Time Test Circuit

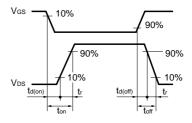


Fig.11 Switching Time Waveforms

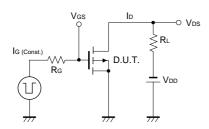


Fig.12 Gate Charge Test Circuit

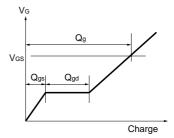


Fig.13 Gate Charge Waveform

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